



IN THE UNITED STATES

**PATENT AND TRADEMARK OFFICE**

APPLICANTS: Yowjuang William Liu and Donald L. Wollesen

PRIOR APPLICATION:

SERIAL NO.: 09/052,057

FILING DATE: March 30, 1998

TITLE: Trenched Gate Non-Volatile Semiconductor Device With The Source/Drain Regions Spaced From the Trench by Sidewall Dopings

EXAMINER: H. Weiss

GROUP ART UNIT: 2814

ATTY. DKT. NO.: 2974

NEW ATTY. DKT. NO. 5251

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner For Patents, Washington, DC 20231, on the date printed below:

Dated: July 21, 2000

By: [Signature]  
Trinidad Arriola Kern, Reg. No.: 44,012

BOX PATENT APPLICATION  
ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to Examination of the above-identified patent application, please amend the above-referenced application as set forth below.

RECEIVED  
NOV 14, 2000  
TECHNOLOGY CENTER 2801